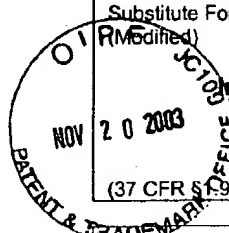


Substitute Form PTO-1449 (Revised)	U.S. Department of Commerce Patent and Trademark Office	Attorney's Docket No. 12967-002001	Application No. 09/824,965
Information Disclosure Statement by Applicant (Use several sheets if necessary) (37 CFR § 1.98(b))		Applicant Tomohiro Kawase et al.	
		Filing Date April 3, 2001	Group Art Unit 1765

**U.S. Patent Documents**

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AL							
	AM							
	AN							
	AO							
	AP							

Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
	D1	Hein, "Growth of Semiinsulating GaAs Crystals by Vertical Gradient Freeze Technique," Crystal Research Technology v. 30, No. 7, pp. 897-909 (1995)
	D1A	Hein et al, "Die Kristallisation und Schmelzen aus metallurgischer Prozess," Metall, v. 47, No. 10, pp. 924-928 (Oct. 1993)
	D2	Flade, "Entwicklung gross flächiger GaAs-Substrate," Freiburger Elektronikwerkstoffe GmbH (Hannover, Germany, February 19, 1996) (?)

Examiner Signature 	Date Considered 2/10/04
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	